Figure 1.1:	Schematics diagram of (a) resistive gas sensor (b) I-V characteristics with and without gas.	6
Figure 1.2:	Schematic diagram of (a) MOS-Capacitor (b) C-V Characteristic with and without gas.	7
Figure 1.3:	Schematic diagram of (a) Metal-semiconductor Schottky diode and (b) I-V Characteristic with and without gas.	7
Figure 1.4:	Schematic diagram of (a) FET and (b) Drain current (I_D) and gate voltage (V_G) with and without gas.	8
Figure 1.5:	Proposed solid-state gas sensors using nanostructures (a) Resistor (b) Schottky diode.	31
Figure 2.1:	The test pattern of thick film gas sensor.	36
Figure 2.2:	A thin film resistor as a gas sensor.	37
Figure 2.3:	A schematic response curve of the gas sensor.	38
Figure 2.4:	Atomically thin transition metal dichalcogenide	42
Figure 2.5:	A long chain molecules made of polymer	43
Figure 2.6:	A view of (a) Carbon nano tube (CNT) (b) grapheme	44
Figure 2.7:	Hexagonal wurtzite structure of Zin Oxide (ZnO).	47
Figure 2.8:	E-K representation of valance and conduction band of ZnO.	48
Figure 2.9:	Physisorption and Chemisorption process on the ZnO Surface.	50
Figure 3.1:	Front view of thick film printer.	52
Figure 3.2:	Front view of electric Oven.	53
Figure 3.3:	Front view of the conveyor belt furnace.	54
Figure 3.4:	Front view of a calcination furnace.	55
Figure 3.5:	Electron beam follows the path through lances	56
Figure 3.6:	X-ray photon being absorbed by an orbital electron.	57
Figure 3.7:	A Schematic of X-ray diffraction pattern.	57

Figure 3.8:	A schematic of the AFM set-up.	59
Figure 3.9:	Front view of In-house developed a measurement system.	60
Figure 3.10:	Resistive sensor fabrication process flow.	61
Figure 3.11:	Flowchart of the synthesis of ZnO nanoparticles.	62
Figure 3.12:	Top view of (a) heater and (b) inter-digited gold electrode	63
Figure 3.13:	Top view of transferred (a) heater (b) electrode pattern in the screen.	64
Figure 3.14:	Top view of (a) front side of brush coated ZnO nanoparticles on gold-electrode (b) rear side of heater pattern on an alumina substrate	65
Figure 3.15:	Schematic Diagram of Gas Sensing Set-up.	66
Figure 3.16:	Images of (a) XRD (b) AFM (C) FE-SEM and (d) EDS of ZnO nanoparticles film.	68
Figure 3.17:	 (a) As the change in the temperature range from 160 to 350 °C the sensitivity(%)/ppt plot of NO₂, H₂, CO ethanol, propanol. (b) Dynamic resistance of ZnO nanoparticles based resistor upon exposure of 0.1 to 0.234 ppt NO2 concentration at 280°C. 	70
Figure 3.18:	(a) Adsorption of oxygen ions on the gains of ZnO before exposure of NO_2 (b) Chemisorption of NO_2 ions after exposing of NO_2 molecules.	71
Figure 3.19:	(a) The dynamic sensitivity of sensor (b) Increase in sensitivity as increase in NO_2 concentration (c) Change in response and recovery time with increasing NO_2 concentration (d) repeatable sensitivity at 280 °C.	72
Figure 4.1:	Front view of Hindhivac 12A4D thermal evaporator.	78
Figure 4.2:	Front view of Thermo-chuck-system.	79
Figure 4.3:	Front view of a Spin Coater.	79
Figure 4.4:	Front view of Bench Furnace.	81
Figure 4.5:	Front view of L117 Gaertner Scientific Corp. ellipsometer.	82
Figure 4.6:	Front view of semiconductor parameter analyzer.	83
Figure 4.7:	Flowchart of the fabrication of Pd/ZnO nanoparticles based Schottky diode.	83

Figure 4.8:	Schematic of Pd/ZnO nanoparticles based Schottky diode.	84
Figure 4.9:	Schematic diagram of NO ₂ measurement set-up.	85
Figure 4.10:	(a) XRD (b) AFM (c) FE-SEM and (d) EDX image of 2 h annealed film of ZnO NPs at 400 °C.	87
Figure 4.11:	(a) I-V characteristics of Pd/ZnO diode. The inset shows the $ln(I)$ vs V plot. (b) Change in ideality factor and barrier height upon exposure to NO ₂ concentration ranging from 10 to 50 ppm at room temperature.	89
Figure 4.12:	Energy band diagram representation of Pd/ZnO Schottky diode upon exposure to NO_2 shows (a) adsorption (b) diffusion (c) formation of dipole moments results change in diode parameters.	91
Figure 4.13:	(a) Transient response of Pd/ZnO Schottky sensor (b) Sensitivity plot (c) response and recovery time of Pd/ZnO sensor upon NO ₂ concentration ranging from 10 to 50 ppm at room temperature.	92
Figure 4.14:	The repeatable transient response of Pd/ZnO Sensor under 10 ppm NO_2 gas.	93
Figure 5.1:	Schematic of H ₂ measurement set-up.	97
Figure 5.2:	(a) I-V characteristics and (b) diode forward current of Pd/ZnO Schottky diode due to change in the temperature range from 75 to 110 °C.	98
Figure 5.3:	I-V characteristics of Pd/ZnO diode at (a) 75 °C (b) 90 °C and (c) 110 °C where inset shows the ln (I) vs V plot. Change in ideality factor and barrier height upon exposure to H ₂ concentration ranging from 200 to 2000 ppm at (d) 75 °C (e) 90 °C (f) 110 °C.	101
Figure 5.4:	Energy band diagram representation for change in barrier height due to H_2 gas molecules.	102
Figure 5.5:	Transient response at (a) 75 °C, (b) 95 °C, (c) 110 °C and (d) Sensitivity Vs temperature plot of Pd/ZnO sensor under- exposure of $200 - 2000$ ppm H ₂ concentration.	104
Figure 5.6:	Effect of temperature on (a) Response time and (b) Recovery time for 200 to 2000 ppm H_2 gas concentration in the temperature range from 75 to 110 °C.	106
Figure 5.7:	The repeatable transient response of Pd/ZnO sensor upon repeatable exposure of 500 ppm hydrogen gas at 90 °C.	107

Figure 6.1:The prospective work can be dong (a) using SCHOTT flexible115substrate (b) under the presence of UV radiation.